





20V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max @ T _A = +25°C (Note 5)	
	495mΩ @ $V_{GS} = -4.5V$	-0.77A	
-20V	690mΩ @ V _{GS} = -2.5V	-0.67A	
	960mΩ @ V _{GS} = -1.8V	-0.57A	

Description and Applications

This MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, which makes it ideal for high-efficiency power management applications.

Portable Electronics

Features and Benefits

- Footprint of Just 0.6mm²—13 Times Smaller Than SOT23
- Low Gate Threshold Voltage
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- ESD Protected Gate
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

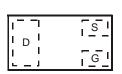
- Case: X1-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—NiPdAu Over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.001 grams (Approximate)



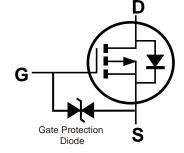




Bottom View



Top View Internal Schematic



Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP21D0UFB-7	X1-DFN1006-3	3,000/Tape & Reel
DMP21D0UFB-7B	X1-DFN1006-3	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, see https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information

DMP21D0UFB-7	Top View Dot Denotes Drain Side From date code 1527 (YYWW), this changes to: Top View Bar Denotes Gate and Source Side
DMP21D0UFB-7B	Top View Bar Denotes Gate and Source Side NG = Part Marking Code



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V_{DSS}	-20	V	
Gate-Source Voltage		V _{GSS}	±8	V	
Continuous Drain Current	Steady State V _{GS} =-4.5V	$T_A = +25^{\circ}\text{C (Note 5)}$ $T_A = +85^{\circ}\text{C (Note 5)}$ $T_A = +25^{\circ}\text{C (Note 6)}$	l _D	-0.77 -0.55 -1.17	А
Pulsed Drain Current (Note 7)		I _{DM}	-5.0	А	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	0.43	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{OJA}	293	°C/W
Power Dissipation (Note 6)	P _D	0.99	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{OJA}	126	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Thermal Characteristics

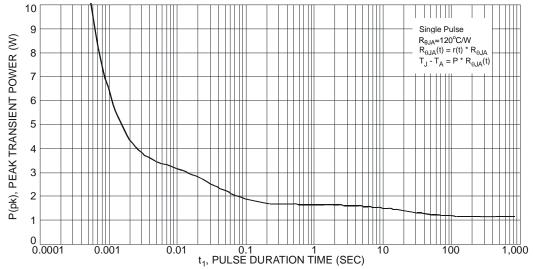
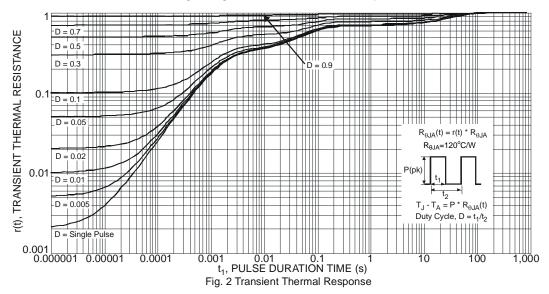


Fig. 1 Single Pulse Maximum Power Dissipation





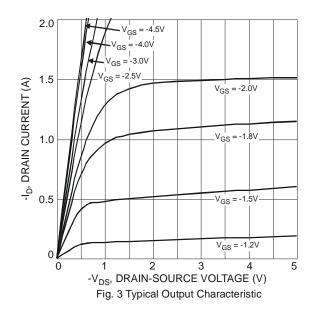
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

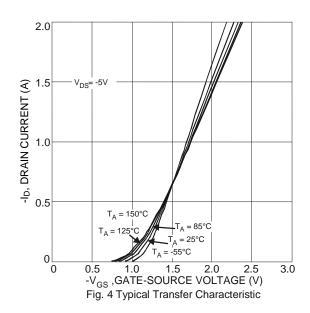
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	-20	1	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current, T _J = +25°C	I _{DSS}	_	1	-1	μA	$V_{DS} = -20V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}		1	±10	μΑ	$V_{GS} = \pm 8V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(TH)}	-0.5	-0.7	-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
			I	495		$V_{GS} = -4.5V$, $I_{D} = -400$ mA	
Static Drain-Source On-Resistance	R _{DS(ON)}		l	690	mΩ	$V_{GS} = -2.5V$, $I_D = -300$ mA	
				960		$V_{GS} = -1.8V, I_{D} = -100mA$	
Forward Transfer Admittance	Y _{fs}	50	1	_	mS	$V_{DS} = -3V, I_{D} = -300 \text{mA}$	
Diode Forward Voltage	V_{SD}		I	-1.2	V	$V_{GS} = 0V, I_{S} = -300mA$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}	_	76.5	_	pF	101/1/	
Output Capacitance	Coss	1	13.7	_	pF	$V_{DS} = -10V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	1	10.7	_	рF		
Gate Resistance	R_{g}	1	195	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Qg	_	1.5		nC	$V_{GS} = -8V, V_{DS} = -15V, I_{D} = -1A$	
Total Gate Charge	Q_{g}	_	1.0	_	nC	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	
Gate-Source Charge	Qgs	_	0.2		nC	$V_{GS} = -4.5V, V_{DS} = -15V,$ $I_{D} = -1A$	
Gate-Drain Charge	Q_{gd}	_	0.3	_	nC		
Turn-On Delay Time	t _{D(ON)}	_	7.1	_	ns		
Turn-On Rise Time	t _R	_	8.0		ns	$V_{DS} = -10V, I_D = -1A$ $V_{GS} = -4.5V, R_G = 6\Omega$	
Turn-Off Delay Time	t _{D(OFF)}	_	31.7	_	ns		
Turn-Off Fall Time	t _F	_	18.5	_	ns		

Notes:

- Device mounted on FR-4 substrate PCB, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PCB, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.
 Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.

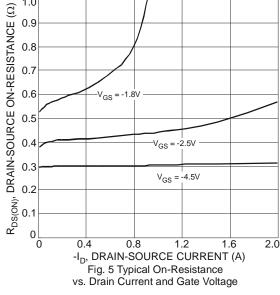
Typical Characteristics

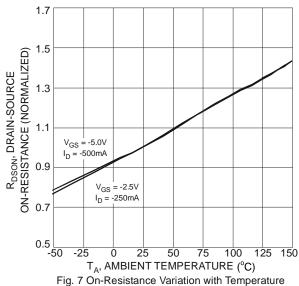


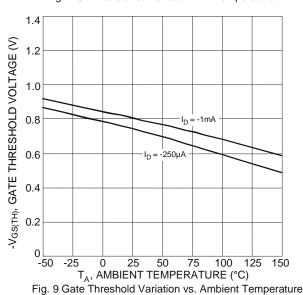




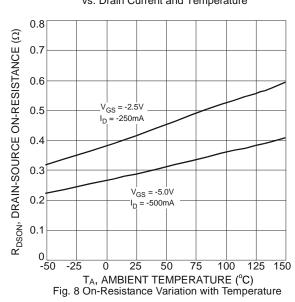








0.8 R_{DS(ON)}, DRAIN-SOURCE ON-RESISTANCE (Ω) 0.6 0.5 = 150°C = 125°C T_A = 85°C = 25°C = -55°C 0 0 2.0 8.0 0.4 1.6 -I_D, DRAIN CURRENT (A) Fig. 6 Typical On-Resistance vs. Drain Current and Temperature



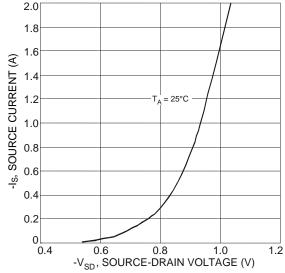
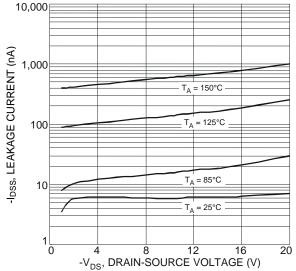
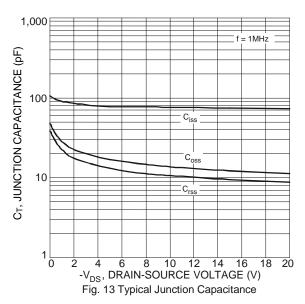


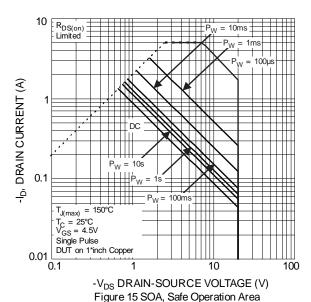
Fig. 10 Diode Forward Voltage vs. Current

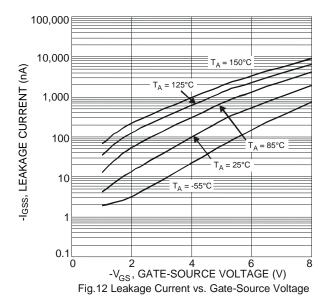


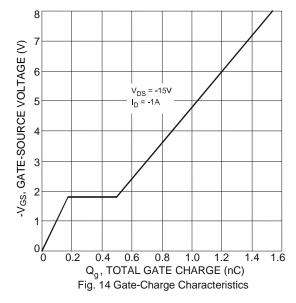


-V_{DS}, DRAIN-SOURCE VOLTAGE (V) Fig. 11 Typical Leakage Current vs. Drain-Source Voltage







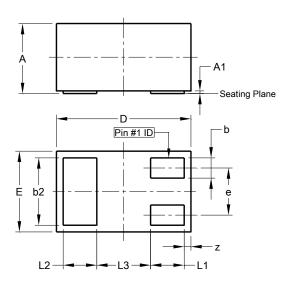




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X1-DFN1006-3

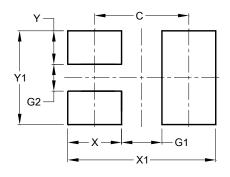


X1-DFN1006-3					
Dim	Min	Max	Тур		
Α	0.47	0.53	0.50		
A1	0.00	0.05	0.03		
b	0.10	0.20	0.15		
b2	0.45	0.55	0.50		
D	0.95	1.075	1.00		
Е	0.55	0.675	0.60		
е	-	-	0.35		
L1	0.20	0.30	0.25		
L2	0.20	0.30	0.25		
L3	-	-	0.40		
Z	0.02	0.08	0.05		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

X1-DFN1006-3



Dimensions	Value (in mm)
С	0.70
G1	0.30
G2	0.20
Х	0.40
X1	1.10
Υ	0.25
Y1	0.70

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